

A cross-sectional view of a semiconductor device 10. The device is shown as a layered structure. At the top is a layer 100 with a diagonal hatching pattern. Below this is a layer 200, which is divided into three horizontal sections: a top section with a cross-hatching pattern, a middle section with a horizontal line pattern, and a bottom section with a diagonal hatching pattern. Below layer 200 is a layer 300 with a stippled pattern. At the bottom is a layer 210 with a diagonal hatching pattern. A bracket labeled 10 spans the top three layers (100, 200, and 300). A bracket labeled 20 spans the entire device structure. A bracket labeled 30 spans the bottom two layers (300 and 210).

A cross-sectional view of a semiconductor device 100. The device is formed on a substrate 20, which is indicated by diagonal hatching. A layer 30 is formed on the substrate 20. The layer 30 is divided into three regions: a first region 100, a second region 200, and a third region 300. The first region 100 is a layer with a stippled pattern. The second region 200 is a layer with a cross-hatched pattern. The third region 300 is a layer with a vertical line pattern. A layer 210 is formed on the first region 100 and the second region 200. The layer 210 is a layer with a cross-hatched pattern. The layer 210 is formed on the first region 100 and the second region 200. The layer 210 is formed on the first region 100 and the second region 200.

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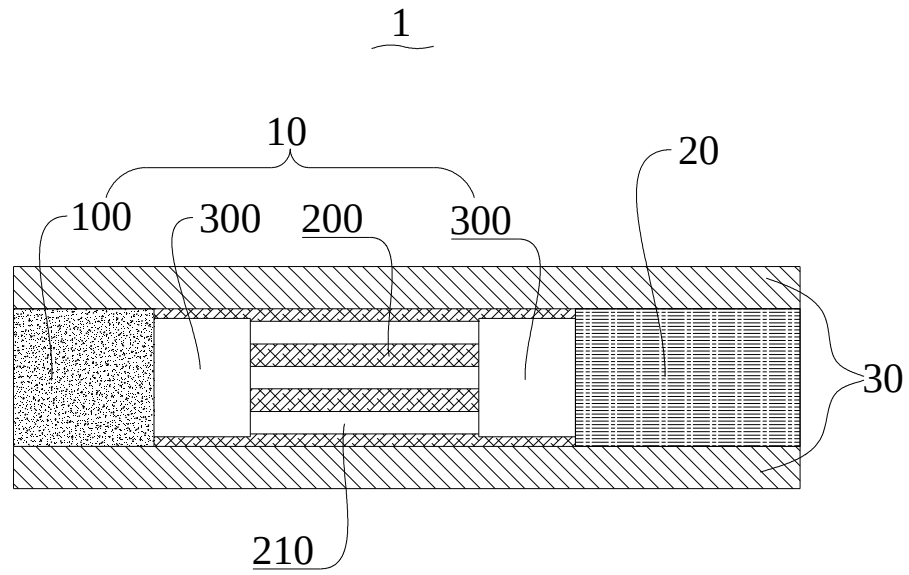


Fig. 3

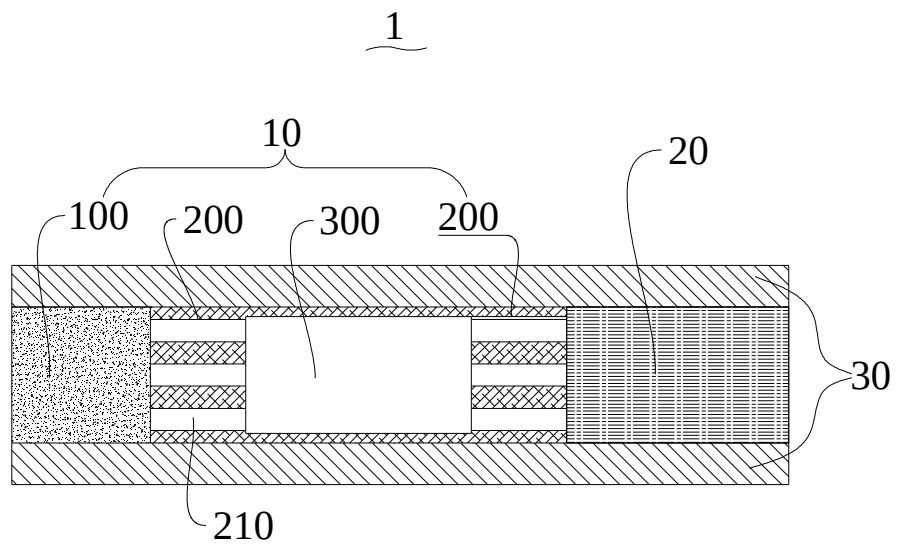


Fig. 4

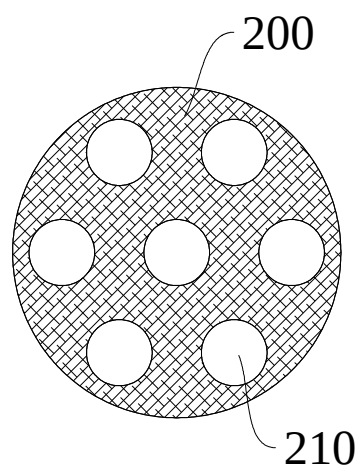


Fig. 5